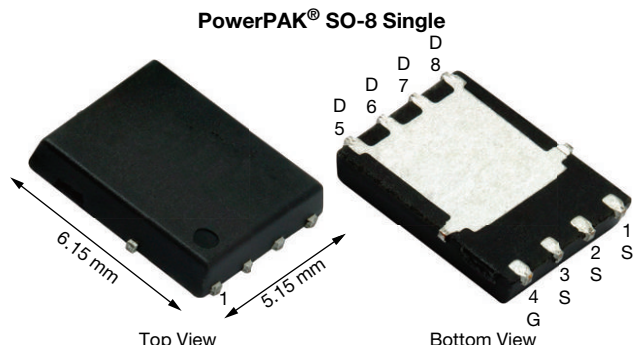


N-Channel 30 V (D-S) MOSFET with Schottky Diode



FEATURES

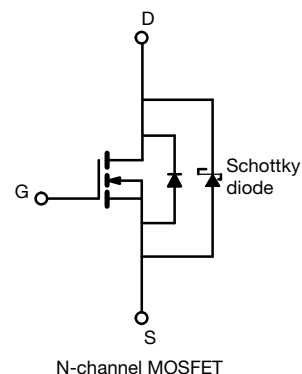
- TrenchFET® Gen IV power MOSFET
- SKYFET® with monolithic Schottky diode
- Optimized $R_{DS(on)}$ - Q_g and $R_{DS(on)}$ - Q_{gd} FOM elevates efficiency for high-frequency switching
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Synchronous buck
- Synchronous rectification
- DC/DC conversion



PRODUCT SUMMARY	
MOSFET	
V_{DS} (V)	30
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10$ V	0.00110
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 4.5$ V	0.00154
Q_g typ. (nC)	35
I_D (A) ^{a, g}	60
SCHOTTKY	
V_F (V) at 10 A	0.55
I_F (A) ^{a, g}	60
Configuration	Single plus integrated Schottky

ORDERING INFORMATION	
Package	PowerPAK SO-8
Lead (Pb)-free and halogen-free	SiRC18DP-T1-GE3

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	30	V
Gate-source voltage	V_{GS}	+20, -16	
Continuous drain current ($T_J = 150$ °C)	I_D	60 ^a	A
		60 ^a	
		52 ^{b, c}	
		42 ^{b, c}	
Pulsed drain current ($t = 100$ μ s)	I_{DM}	250	
Continuous source current (MOSFET diode conduction)	I_S	60 ^a	
		5 ^{a, b}	
Single pulse avalanche current	I_{AS}	30	mJ
Single pulse avalanche energy	E_{AS}	45	
Maximum power dissipation	P_D	54.3	W
		34.7	
		5 ^{b, c}	
		3.2 ^{b, c}	
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +150	°C
Soldering recommendations (peak temperature)		260	

**THERMAL RESISTANCE RATINGS**

PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient ^{b, f}	$t \leq 10$ s	R_{thJA}	20	25	°C/W
Maximum junction-to-case (drain)	Steady state	R_{thJC}	1.8	2.3	

Notes

- a. Package limited
b. Surface mounted on 1" x 1" FR4 board
c. $t = 10$ s
d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
f. Maximum under steady state conditions is 65 °C/W
g. $T_C = 25$ °C

SPECIFICATIONS ($T_J = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	30	-	-	V
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	1	-	2.4	
Gate-source leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = +20\text{ V}$, -16 V	-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 30\text{ V}$, $V_{GS} = 0\text{ V}$	-	0.06	0.10	mA
		$V_{DS} = 30\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 70\text{ }^{\circ}\text{C}$	-	1	10	
On-state drain current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}$, $V_{GS} = 10\text{ V}$	40	-	-	A
Drain-source on-state resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 15\text{ A}$	-	0.00085	0.00110	Ω
		$V_{GS} = 4.5\text{ V}$, $I_D = 10\text{ A}$	-	0.00135	0.00154	
Forward transconductance ^a	g_{fs}	$V_{DS} = 10\text{ V}$, $I_D = 15\text{ A}$	-	70	-	S
Dynamic ^b						
Input capacitance	C_{iss}	$V_{DS} = 15\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$	-	5060	-	pF
Output capacitance	C_{oss}		-	2400	-	
Reverse transfer capacitance	C_{rss}		-	350	-	
C_{rss}/C_{iss} ratio			-	0.069	0.140	
Total gate charge	Q_g	$V_{DS} = 15\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 10\text{ A}$	-	74	111	nC
Gate-source charge	Q_{gs}	$V_{DS} = 15\text{ V}$, $V_{GS} = 4.5\text{ V}$, $I_D = 10\text{ A}$	-	35	53	
Gate-drain charge	Q_{gd}		-	11.8	-	
Gate resistance	R_g		-	8.4	-	
Gate resistance	R_g	$f = 1\text{ MHz}$	0.1	0.5	0.9	Ω
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 15\text{ V}$, $R_L = 1.5\text{ }\Omega$, $I_D \equiv 10\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 1\text{ }\Omega$	-	16	32	ns
Rise time	t_r		-	21	42	
Turn-off delay time	$t_{d(off)}$		-	30	60	
Fall time	t_f		-	12	24	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 15\text{ V}$, $R_L = 1.5\text{ }\Omega$, $I_D \equiv 10\text{ A}$, $V_{GEN} = 4.5\text{ V}$, $R_g = 1\text{ }\Omega$	-	31	62	
Rise time	t_r		-	77	154	
Turn-off delay time	$t_{d(off)}$		-	38	76	
Fall time	t_f		-	37	74	
Drain-source Body Diode Characteristics						
Continuous source-drain diode current	I_S	$T_C = 25^{\circ}\text{C}$	-	-	60	A
Pulse diode forward current	I_{SM}		-	-	100	
Body diode voltage	V_{SD}	$I_S = 5\text{ A}$, $V_{GS} = 0\text{ V}$	-	0.41	0.55	V
Body diode reverse recovery time	t_{rr}	$I_F = 10\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $T_J = 25\text{ }^{\circ}\text{C}$	-	58	116	ns
Body diode reverse recovery charge	Q_{rr}		-	72	144	nC
Reverse recovery fall time	t_a		-	26	-	ns
Reverse recovery rise time	t_b		-	32	-	

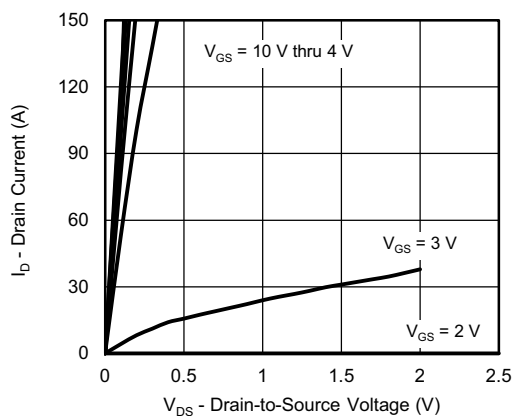
Notes

- a. Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %
b. Guaranteed by design, not subject to production testing

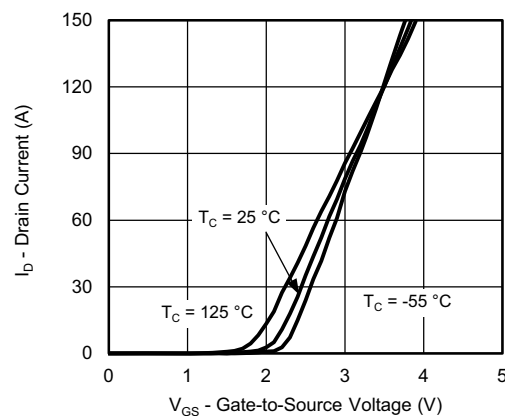
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



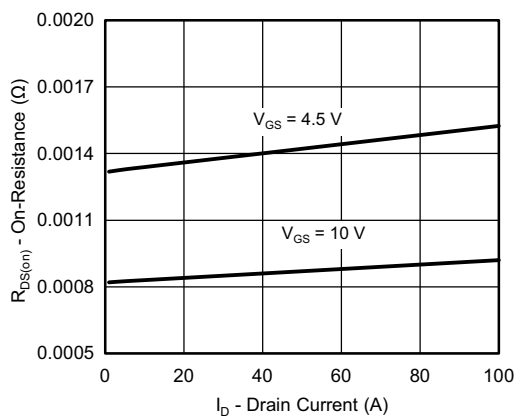
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



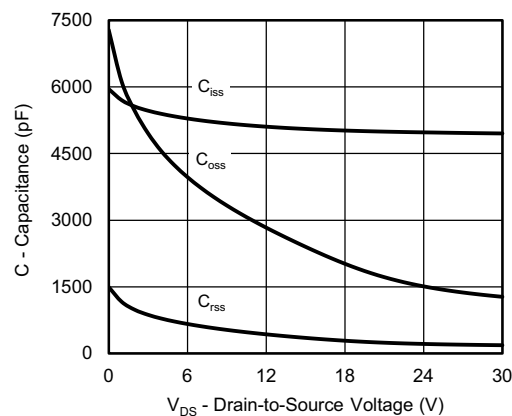
Output Characteristics



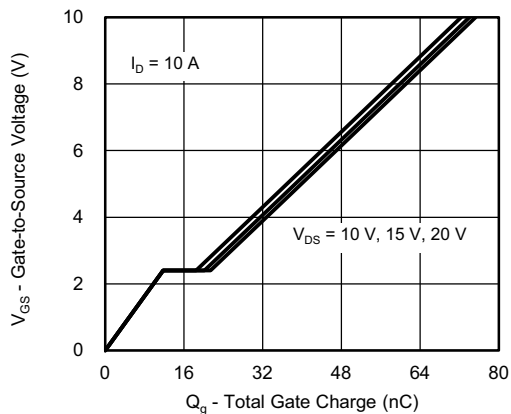
Transfer Characteristics



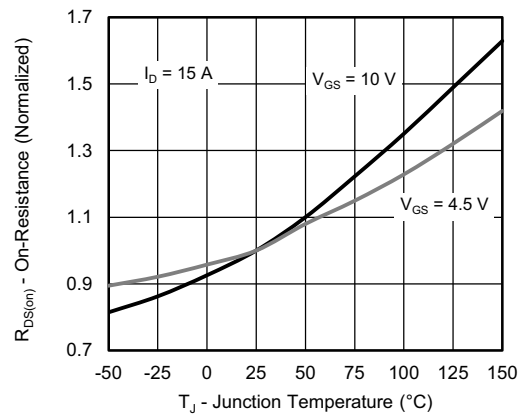
On-Resistance vs. Drain Current and Gate



Capacitance



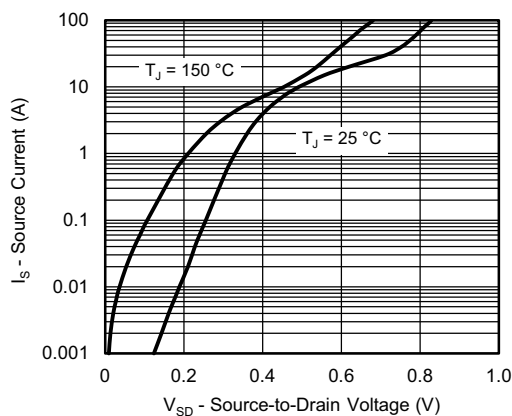
Gate Charge



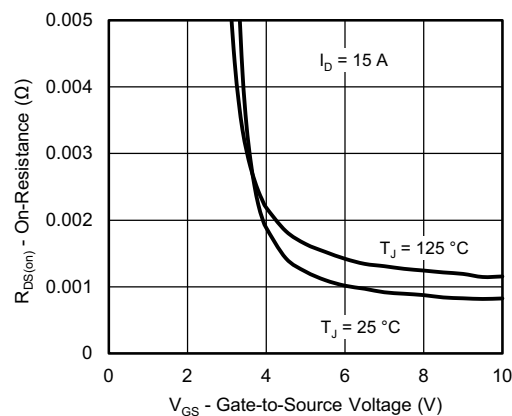
On-Resistance vs. Junction Temperature



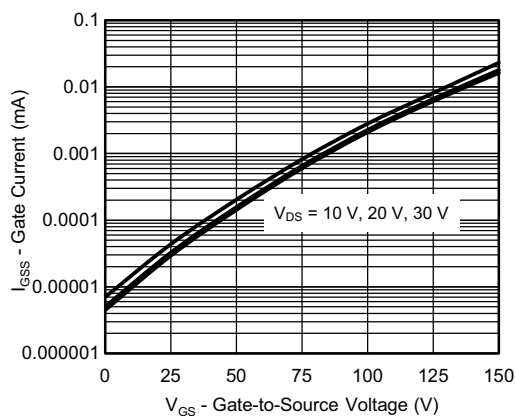
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



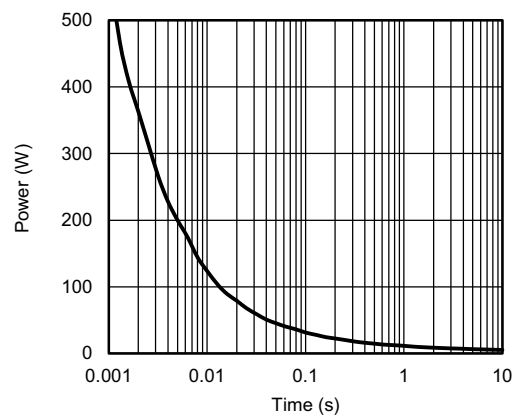
Source-Drain Diode Forward Voltage



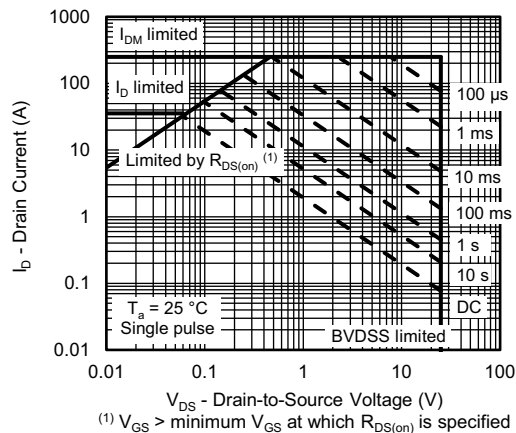
On-Resistance vs. Gate-to-Source Voltage



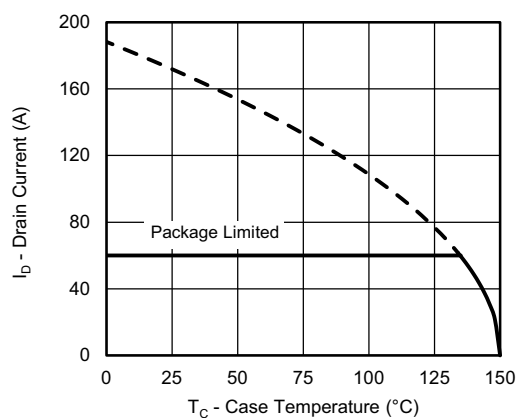
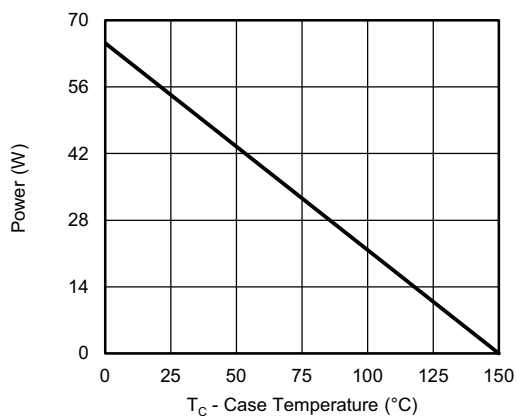
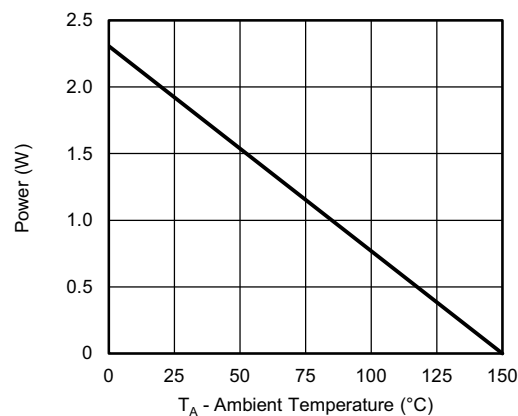
Reverse Current vs. Junction Temperature



Single Pulse Power



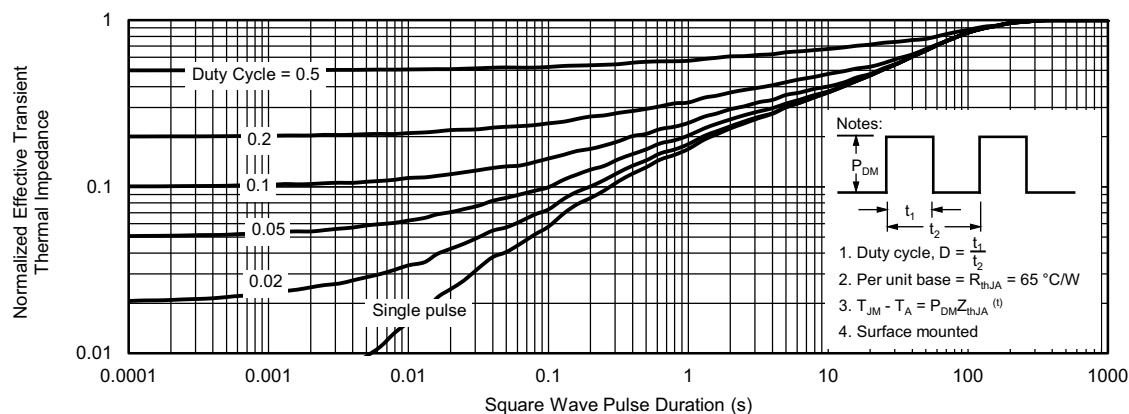
Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Current Derating ^a

Power, Junction-to-Case

Power, Junction-to-Ambient
Note

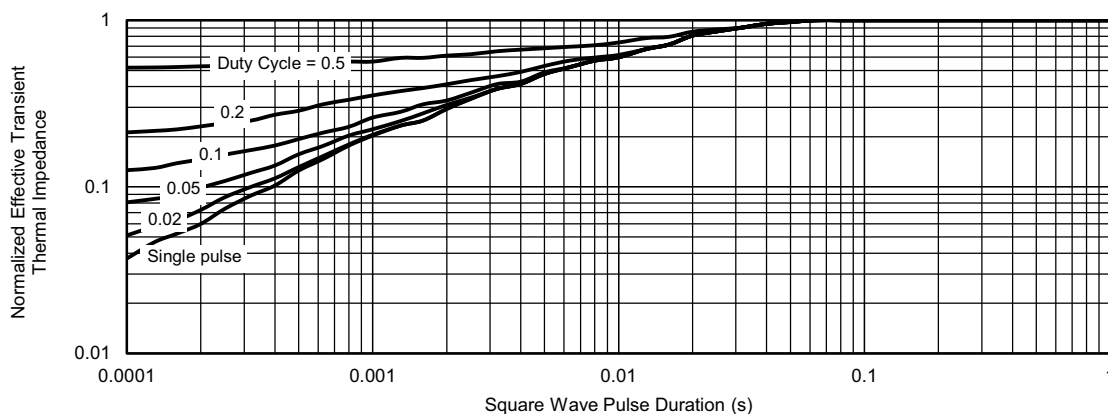
- a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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